

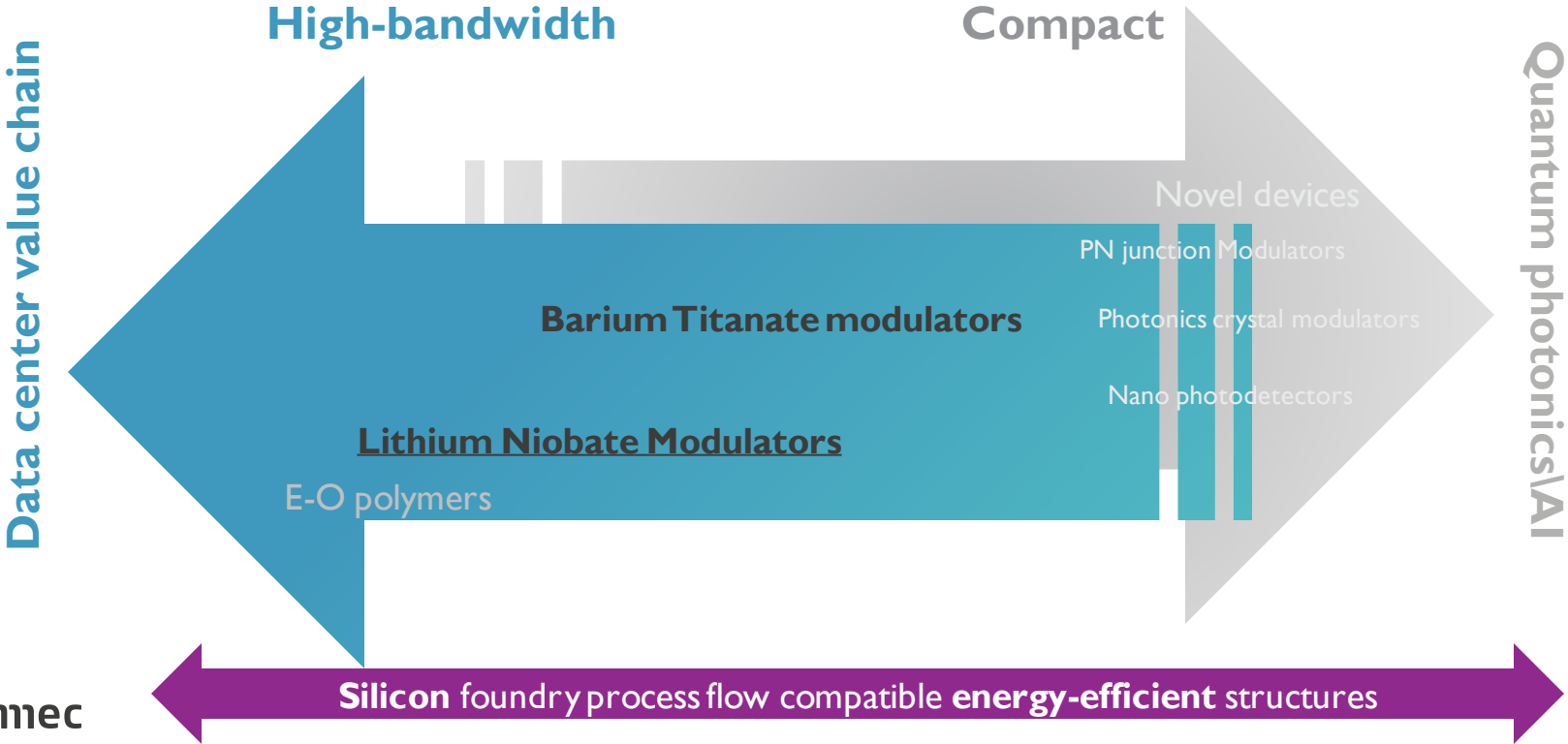


E-O MATERIALS AND DEVICES FOR DATA CENTER AND QUANTUM  
PHOTONICS APPLICATIONS

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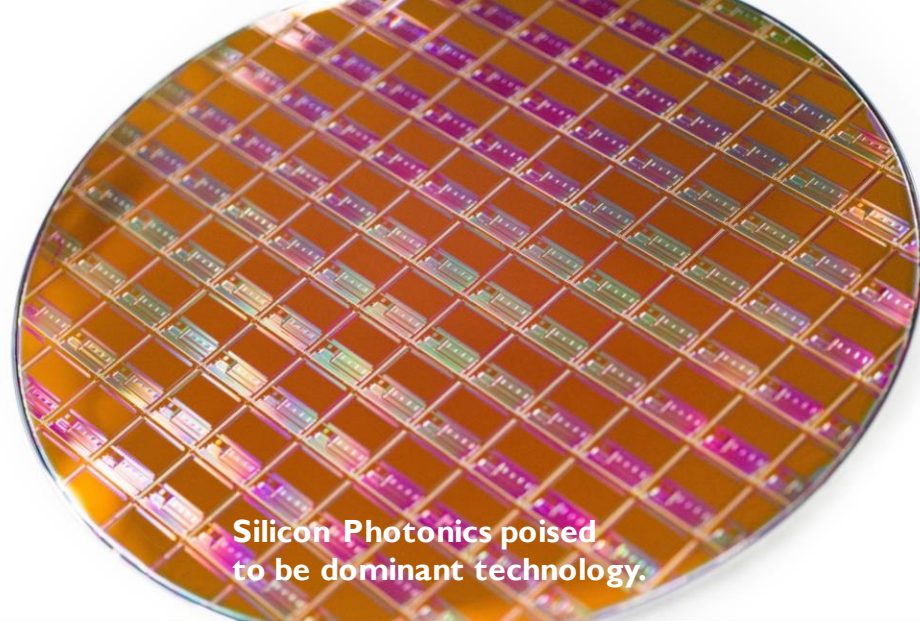
# E-O MATERIALS AND DEVICES RESEARCH

## HIGH-PERFORMANCE INTEGRATED PHOTONIC ELECTRO-OPTIC DEVICES





DCI primary driver  
of Optical Transceivers.

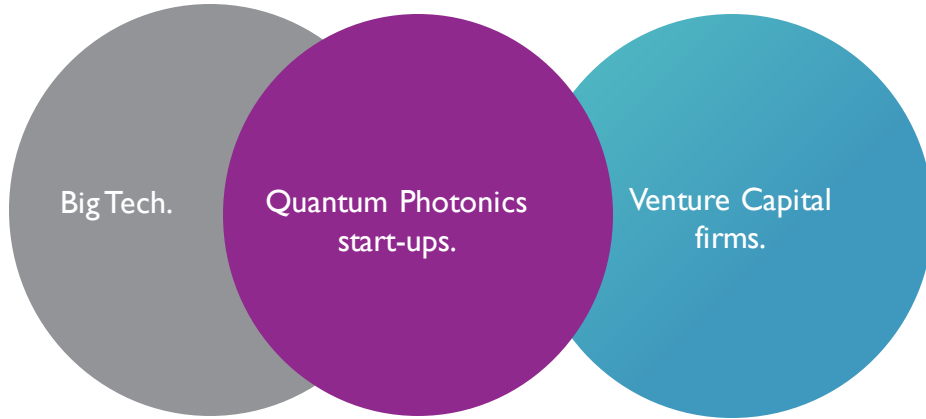


Silicon Photonics poised  
to be dominant technology.

**IEEE 2020 bandwidth assessment indicates need for 1.6Tbps.**

**Reaching limitations for bandwidths silicon-based modulators.**

**High bandwidth modulators based on silicon photonics with post-processed electro-optic materials**



A collage of quantum technology logos and funding information. At the top is a purple bar with 'Xanadu'. Below it is a teal bar with 'PsiQuantum'. In the center is a dark blue box with a padlock icon and the text 'QUANTUM TECHNOLOGIES The most advanced benefits, not possible using conventional hardware.' To the right is a white triangle icon. Further right is a circular logo with 'AAAA' and 'VVVV' around a central gear-like shape. Below this is a dark grey box with the text: 'National Science Foundation (NSF)– Mid-scale quantum photonics infrastructure capabilities seeking foundry partnerships for large scale circuits Air Force Research Lab (AFRL) interested in non-resistive E-O phase shifters'. On the far right edge, there is a small 'S' and 'standard'.

Investments have quadrupled in the past 5 years.

Silicon based quantum technologies are getting bulk of the investment.

Next 10 years will focus on viability at scale and path to commercialization.

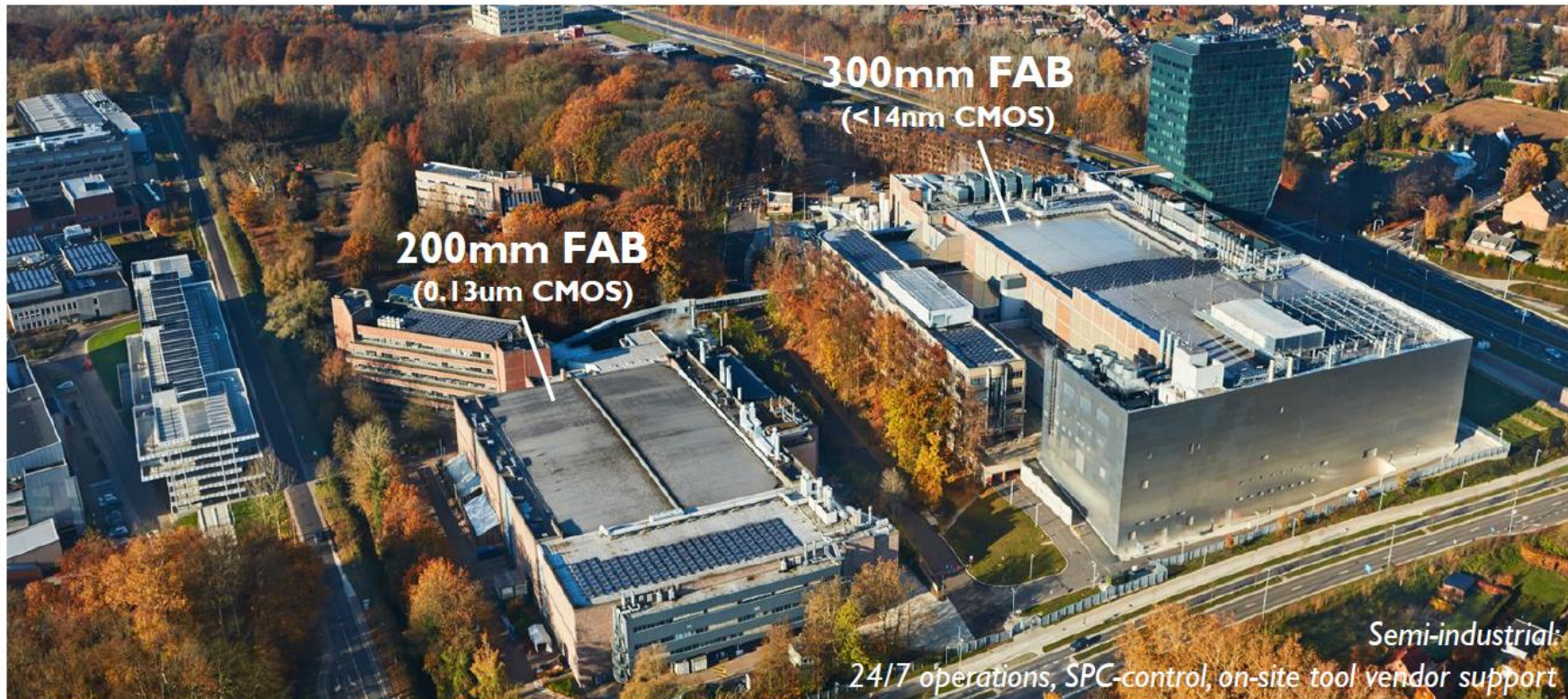
Silicon Photonics could be that path.

Energy efficient, compact phase shifters based on silicon photonics with post-processed electro-optic materials



# IMEC's State-of-the-Art Fabrication Facilities

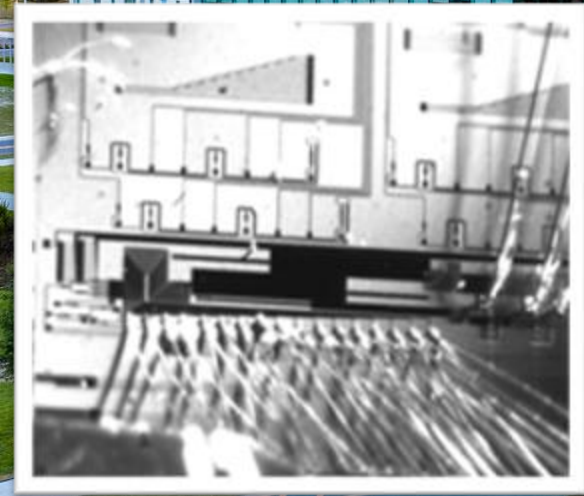
@Leuven Headquarters (25km east of Brussels, Belgium)



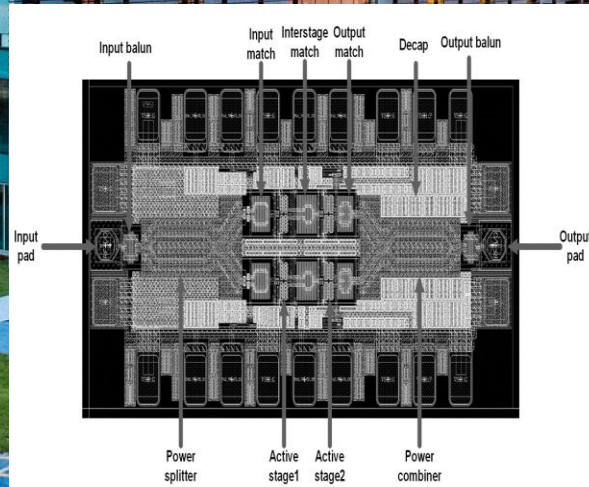
- Silicon Photonics Prototyping in 200mm FAB
- Advanced Silicon Photonics R&D (mostly) in 300mm FAB



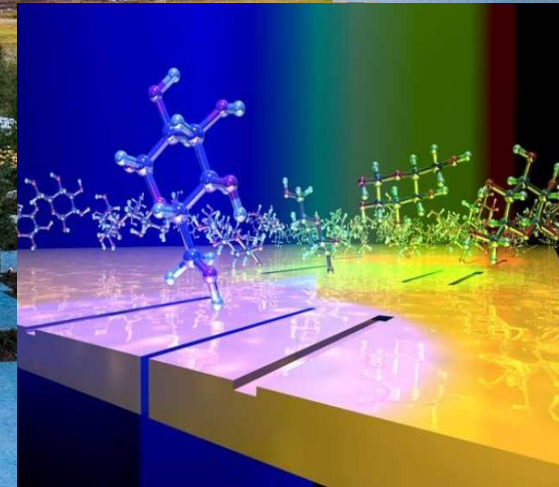
# Imec-USA Nanoelectronics Design Center.



Photonics Design.



Electronics Design.



Electro-optic materials and process flows.

# HI-PED PROGRAM OBJECTIVES

Integrated Modulator Performance Targets		Year 1 (2020-2021)	Year 2 (2021-2022)	Year 3 (2022-2023)
	RF Bandwidth	50GHz	70GHz	100GHz
	Operating Wavelengths	C,L,O	C, L,O	C, L, O
	Target V <sub>pi</sub> -L	3V-cm (2V-cm)	2V-cm (1V-cm)	<1V-cm (<0.5 V-cm)
	Insertion Loss (fiber-to-fiber)	<6dB	<4dB	<2dB

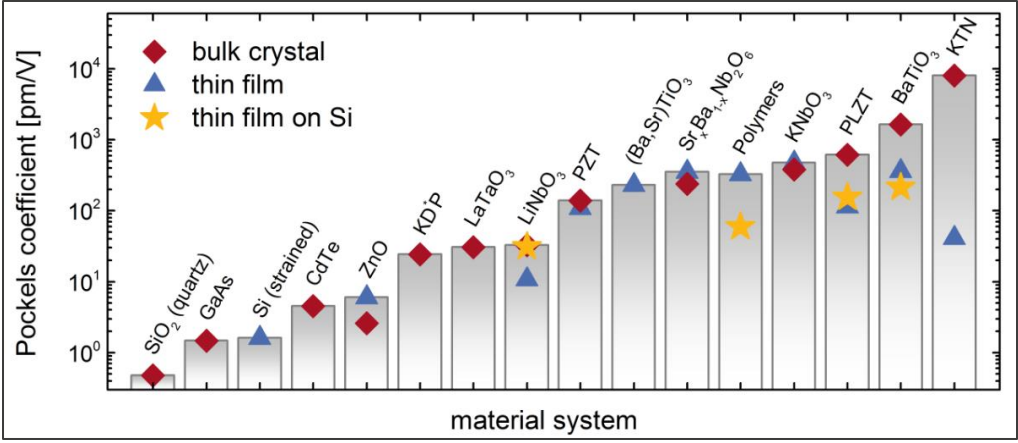
Explore silicon photonics foundry compatible electro-optical material integration processes and structures for the development of compact, energy-efficient, ultra-high-performance modulators for communication, and compute applications targeting 100GHz bandwidth and CMOS compatible drive voltages

# **TECHNOLOGY OVERVIEW.**



**CURRENT STATE OF THE ART.**

# ELECTRO-OPTIC MATERIALS



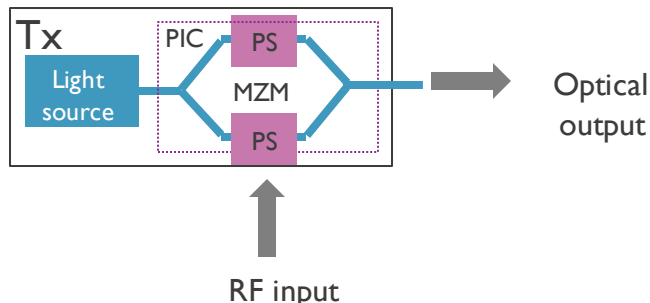
URL: <https://www.zurich.ibm.com/st/photonics/materials.html>

Abel et al., “A strong electro-optically active lead-free ferroelectric integrated on silicon”, Nature Comm. 4, 1671 (2013)

Abel et al., “A Hybrid Barium Titanate–Silicon Photonics Platform for Ultraefficient Electro-Optic Tuning”, J. Lightwave Tech. 34(8), 1688 (2016)

**THIN FILM LITHIUM NIOBATE RESEARCH TRACK.**

# WHY TFLN - COMPACT HYBRID SILICON EO-MATERIAL MZM

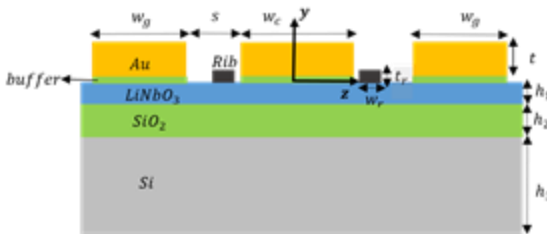


	<b>Silicon modulators</b>	<b>Conventional LN</b>	<b>LN on Silicon</b>
Length (mm)	< 6	> 60	8
$V_{\pi}L$ (V.cm)	2 to 3	> 10	2 to 3
Optical loss (dB/cm)	~ 1	0.3	<0.4
Extinction ratio (dB)	~ 10	> 20	>20
RF bandwidth (GHz)	> 40	> 100	> 100
Power Handling	10mW	>200mW	>1W
Integrability with silicon photonics	Yes	No	Yes
Linearity	No	Yes	Yes



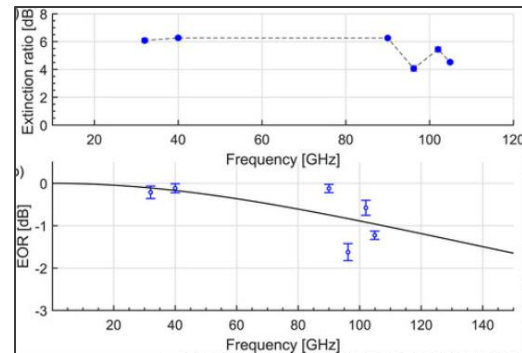
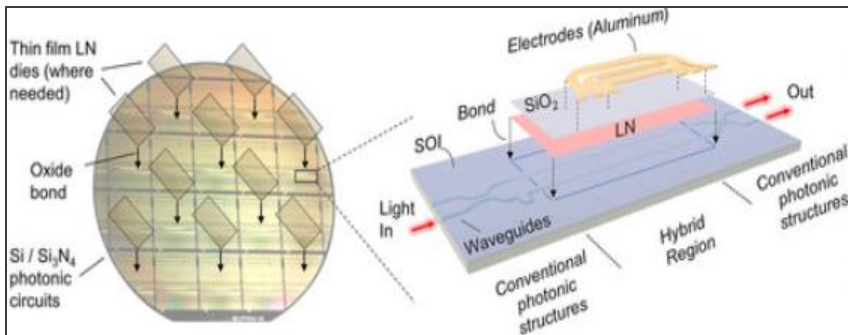
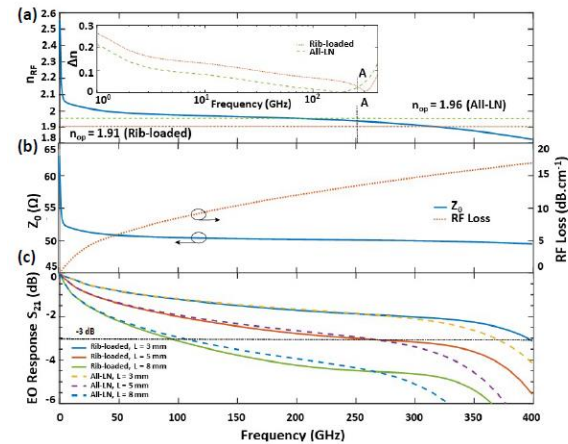
# PRIOR ART TFLN

- Optimized modulator structure for low power design
  - Asymmetrical optical waveguides
    - Electrode spacing optimized to **reduce RF loss**
      - Addition of SiO<sub>2</sub> buffer layer between LN and gold
    - Buffer layer between electrodes to **lower optical loss**
  - Targeting bandwidth larger than 100GHz



Honardoost, et.al., "Towards subterahertz bandwidth ultracompact lithium niobate electrooptic modulators", Opt. Exp. 27 (5), 6495 (2019)

## FOUNDRY COMPATIBLE FABRICATION LACKING at present DUE TO LITHIUM RELATED ISSUES



Mookherjee, et.al., "Achieving beyond-100-GHz large-signal modulation bandwidth in hybrid silicon photonics Mach Zehnder modulators using thin film lithium niobate", APL Photonics 4, 096101 (2019) (Sandia, UCSD)

# CALL TO ACTION

## IN CONCLUSION

- What makes the research program interesting?
  - Pre-competitive research track enabling longer term roadmaps for industry partners
  - Pure phase shift modulators
  - Ultra-high bandwidth (100GHz+) devices
  - Integration with 200mm and 300mm Silicon foundry platforms
  
- Imec proposes research roadmap & invites the industry
  - Inviting industry partners in the data center space and quantum photonics space
  - Partners subscribe to the full program or parts thereof and can request additional specific work next to the program



at imec, we shape the future